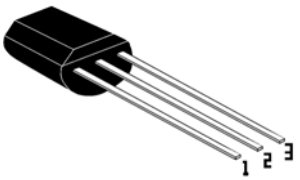
CHANG JIANG
ELECTRONICS CO., LTD.

2N2907

GENERAL PURPOSE TRANSISTOR

* Complement to 2N2222
* Collector-Emitter Voltage V_{CEO}=-40V
* Collector Dissipation Pc=625 mW (Ta=25℃)
* High Collector Current $Ic_{(max)}$ =-600mA

TO-92



1：Emiter
2：Base
3：Collector

ABSOLUTE MAXIMUM RATINGS at Tamb=25℃

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	Vcbo	-60	V
Collector-Emitter Voltage	Vceo	-40	V
Emitter-Base Voltage	Vebo	-5	V
Collector Current	Ic	-600	mA
Collector Dissipation	Pc	625	mW
Junction Temperature	Tj	150	℃
Storage Temperature	Tstg	-55~150	℃

ELECTRICAL CHARACTERISTICS at Tamb=25℃

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BVcbo	-60			V	Ic=-10uA Ie=0
Collector-Emitter Breakdown Voltage#	BVceo	-40			V	Ic=-10mA Ib=0
Emitter-Base Breakdown Voltage	BVebo	-5			V	Ie=-10uA Ic=0
Collector Cutoff Current	Icbo			-20	nA	Vcb=-50V Ie=0
DC Current Gain	Hfe_1	35				Vce=-10v Ic=-0.1mA
DC Current Gain	Hfe_2	50				Vce=-10v Ic=-1mA
DC Current Gain	Hfe_3	75				Vce=-10v Ic=-10mA
DC Current Gain#	Hfe_4	100		300		Vce=-10v Ic=-150mA
DC Current Gain#	Hfe_5	30				Vce=-10v Ic=-500mA
Collector-Emitter Saturation Voltage#	Vce(sat)			-0.4	V	Ic=-150mA Ib=-15mA
Collector-Emitter Saturation Voltage#	Vce(sat)			-1.6	V	Ic=-500mA Ib=-50mA
Base-Emitter Saturation Voltage#	Vbe(sat)			-1.3	V	Ic=-150mA Ib=-15mA
Base-Emitter Saturation Voltage#	Vbe(sat)			-2.6	V	Ic=-500mA Ib=-50mA
Output Capacitance	Cob			8. 0	pF	Vcb=-10V Ie=0 f=1MHz
Current Gain-Bandwidth Product	fT	200			MHz	Vce=-20V Ic=-50mA f=100MHz

Pulse Test : Pulse Width ≦300uS, Duty Cycle≦2%